## NSN 5961-01-294-5732

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Inclosure Material:
Metal
Overall Length:
2.637 inches
Mounting Facility Quantity:
1
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Features Provided:
Burn in
Overall Width Across Flats:
Between 1.031 inches and 1.063 inches
Thread Size:
0.500 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
1000.0 repetitive peak reverse voltage, peak total value and 1200.0 nonrepetitive peak reverse voltage, peak total value
Current Rating Per Characteristic:
1200.00 amperes source cutoff current peak
Power Rating Per Characteristic:
2.0 watts any acceptable universal and 100.0 watts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
125.0 degrees celsius junction
Thread Series Designator:
Unf
Terminal Type And Quantity:
1 threaded stud and 2 tab, solder lug
Shelf Life:
N/a
Unit Of Measure:
<del></del>
Demilitarization:
No
Fiig:
A110a0